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IN THE SPECIFICATION

On page 2 line one please insert -- This is a Divisional Application of

Serial No. 09/115,405 filed on July 14, 1998 which is a Divisional Application of

Serial No. 08/884,912 filed on June 30, 1997. --

IN THE CLAIMS:

Please cancel Claims 1-29 without prejudice.

Please add the following claims.

1 30. A semiconductor device comprising:
2 a gate electrode formed on a gate dielectric formed on a substrate surface,
3 the gate electrode having a first thickness;
4 a gate silicon germanium film formed on the gate electrode, the gate
5 silicon germanium film having a second thickness;
6 a gate silicide layer formed on the gate silicon germanium film, the silicide
7 layer having a third thickness;
8 a pair of sidewall spacers on opposite sides of the gate electrode, the
9 sidewall spacers having a first height above the substrate surface, the first height
10 greater than the sum of the first and second and third thicknesses.

1 31. The semiconductor device of claim 30, wherein the gate electrode is
2 polysilicon.

1 32. The semiconductor device of claim 30, further comprising:
2 a pair of source and drain regions formed on opposite sides of the gate
3 electrode.

1 33. A semiconductor device comprising:
2 a pair of source/drain regions formed on opposite sides of a silicon gate
3 electrode;
4 a silicon germanium film formed on the source/drain regions; and
5 a silicide layer formed on the silicon germanium film.

1 34. The semiconductor device of claim 33 further comprising:
2 an isolation region having a top surface positioned below the germanium
3 film.

1 35. The semiconductor device of claim 33 further comprising:
2 an isolation region having a top surface positioned below the silicide
3 layer.

1 36. A semiconductor device comprising:
2 a silicon gate electrode formed on a gate dielectric formed on a substrate
3 surface, the silicon gate electrode having a first thickness;
4 a gate silicon germanium film formed on the silicon gate electrode, the
5 gate silicon germanium film having a second thickness;
6 a gate silicide layer formed on the gate silicon germanium film, the gate
7 silicide layer having a third thickness, the third thickness greater than the first
8 thickness;
9 a pair of sidewall spacers on opposite sides of the silicon gate electrode,
10 the sidewall spacers having a first height above the substrate surface, the first
11 height greater than the sum of the first and second and third thicknesses;
12 a pair of source/drain regions formed on opposite sides of the silicon gate
13 electrode;
14 a source/drain silicon germanium film formed on the source/drain
15 regions; and
16 a source/drain silicide layer formed on the source/drain silicon
17 germanium film.

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1 37. The semiconductor device of claim 36 wherein the silicon
2 gate electrode is polysilicon.

38. A method of forming a semiconductor device comprising:
forming a gate electrode having a first thickness on a gate dielectric layer
formed on a first surface of a substrate;
forming a pair of source/drain regions on opposite sides of the gate
electrode;
forming a silicon germanium film having a second thickness on the gate
electrode;
forming a silicon germanium film having the second thickness on the
source/drain regions;
forming a silicide layer having a third thickness on the silicon germanium
films.

39. The method of claim 38 further comprising:
forming a pair of sidewall spacers having a first height above the substrate
surface on opposite sides of the gate electrode, wherein the first height is greater
than the sum of the first and second and third thicknesses.

40. The method of claim 39, wherein the sidewall spacers comprise
silicon nitride.

41. A method of forming a semiconductor device, comprising:
forming an isolation region having a top surface in a semiconductor
substrate;
etching the semiconductor substrate adjacent to the isolation region to
form a recess region;
depositing a silicon germanium film having a top surface in the recessed
region; and

8 depositing a silicide layer having a top surface over the silicon germanium
9 film.

1 42. The method of forming a semiconductor device of claim 41,
2 wherein the silicide layer top surface extends above the isolation region top
3 surface.

1 43. The method of forming a semiconductor device of claim 42,
2 wherein the silicon germanium film top surface extends above the isolation
3 region top surface.

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